

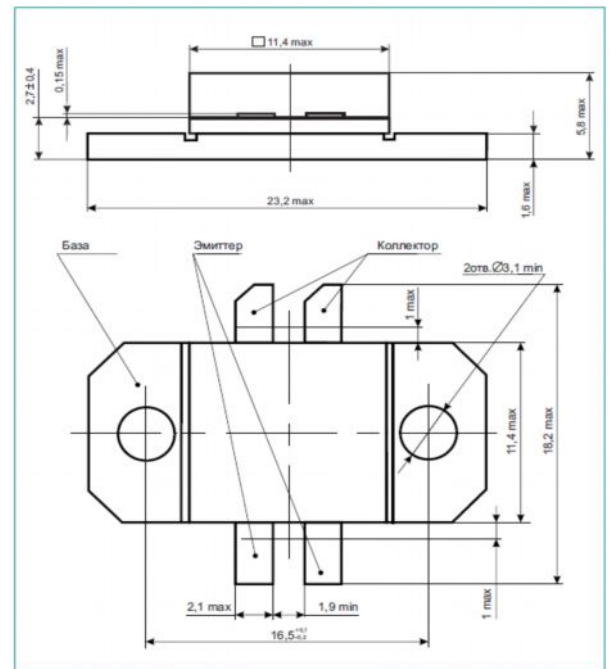
NPN SILICON RF POWER TRANSISTOR

Designed for wideband large-signal
Class AB linear amplifier applications
in power FM equipment operating to 1GHz

- Output power = 50 W, $f = 1000$ MHz, $V_{CC} = 28$ V
- Power gain = 6 dB (min)
- Efficiency = 50% (min)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CER}	50	V
Emitter-Base Voltage	V_{EBO}	3	V
Collector Current	I_C	10	A
Operating Junction Temperature	T_j	+200	°C
Storage Temperature Range	T_{stg}	-65 to +150	°C
Thermal Resistance (junction to case)	$R_{\theta JC}$	1.7	°C/W
Total Power Dissipation, $T_C=25$ °C	P_D	103	W



Case KT-44

FUNCTIONAL TESTS

Characteristics	Symbol	Value			Unit
		min	typ	max	
Common-Emitter Amplifier Power Gain ($V_{CC} = 28$ V, $P_{out} = 50$ W @ 1 dB Comp., $f = 1000$ MHz)	G_P	6			dB
Collector Efficiency ($V_{CC} = 28$ V, $P_{out} = 50$ W, $f = 1000$ MHz)	η_C	50			%

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Specification is subject to change without notice